NSN 5961-01-203-9475

Thyristor Semiconductor Device - Page 1 of 2

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Inclosure Material:

Metal

Overall Length:

1.810 inches

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-83

Mounting Method:

Threaded stud

Overall Width Across Flats:

1.227 inches

Thread Size:

0.500 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

600.0 repetitive peak reverse voltage and 600.0 repetitive peak off-state voltage and 720.0 nonrepetitive peak reverse voltage

Current Rating Per Characteristic:

50.00 amperes forward current, total rms universal

Power Rating Per Characteristic:

0.5 watts small-signal input power, common-collector absolute

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius junction

Special Features:

Junction pattern arrangement: pnpn

Test Data Document:

81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Thread Series Designator:

Unf

Terminal Type And Quantity:

2 tab, solder lug and 1 threaded stud

Specification Data:

81349-mil-prf-19500 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0

Mil-std (military Standard):

Mil-prf-19500 spec.